



60V PNP HIGH PERFORMANCE TRANSISTOR IN PowerDI3333-8

Features

- BV_{CEO} > -60V
- Small Form Factor Thermally Efficient Package.
 Enables Higher Density End Products
- I_C = -3A High Continuous Current
- I_{CM} = -6A Peak Pulse Current
- Low Saturation Voltage V_{CE(SAT)} < -250mV @ -1A
- Complementary NPN Type: DXTN07060BFG
- Rated to +175°C Ideal For High Temperature Environment
- Wettable Flank For Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic. "Green" Molding Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.03 grams (Approximate)

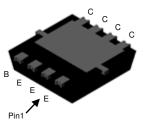
Applications

- High Side Switch
- MOSFET or IGBT Gate Driver

PowerDI3333-8 (SWP) (Type UX)

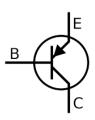


Top View



Bottom View

Equivalent Circuit



Device Symbol

Ordering Information (Note 4)

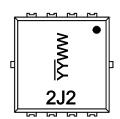
Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DXTP07060BFG-7	AEC-Q101	2J2	7	12	2,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

PowerDI3333-8 (SWP) (Type UX)



2J2= Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 18 = 2018)

WW = Week Code (01 to 53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-3	A
Peak Pulse Current	Ісм	-6	A

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Note 5)		0.9	W
Power Dissipation	(Note 6)	P _D	2.1	W
	(Note 7)		3.1	W
	(Note 5)		140	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	65	°C/W
	(Note 7)		44	°C/W
Thermal Resistance, Junction to Leads (Note 8)		$R_{\theta JL}$	8.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C	

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

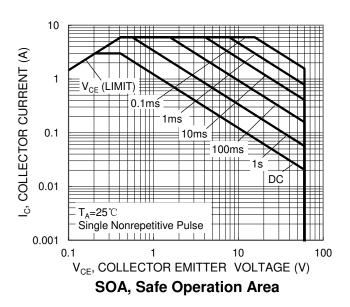
For a device mounted with the collector tab on MRP FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.

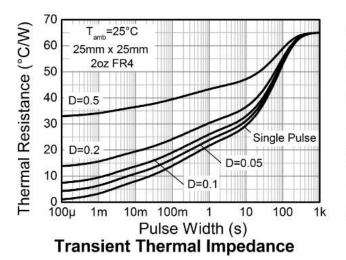
Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper. Notes: 5. 6. 7.

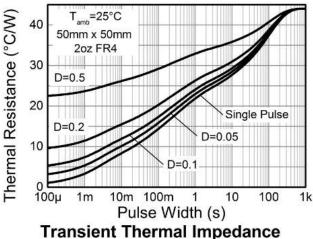
- Thermal resistance from junction to solder-point (at the collector tab). Refer to JEDEC specification JESD22-A114 and JESD22-A115. 8.

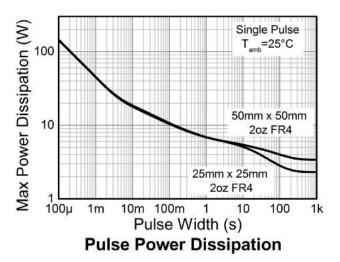


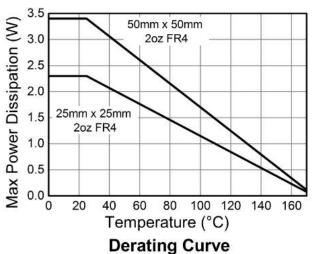
Thermal Characteristics and Derating Information













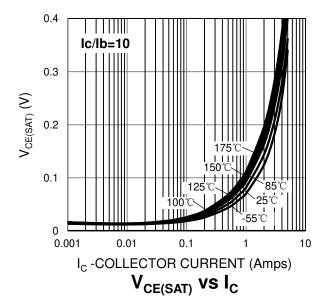
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

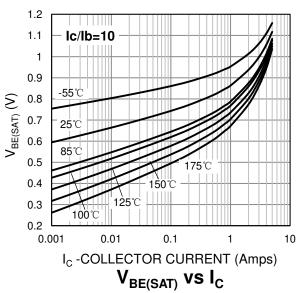
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage	BV _{CBO}	-80	-130	_	V	$I_{C} = -100 \mu A$	
Collector-Emitter Breakdown Voltage (Note 10)	BV_CEO	-60	-88	_	V	I _C = -10mA	
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.3	_	V	$I_E = -100 \mu A$	
Collector Cut-off Current	1	_	_	-20	nA	V _{CB} = -60V	
Collector Cut-on Current	I _{CBO}	_	_	-10	μΑ	$V_{CB} = -60V, T_A = +125^{\circ}C$	
Emitter Cut-off Current	I_{EBO}	_	_	-20	nA	$V_{EB} = -6V$	
Collector-Emitter Saturation Voltage (Note 10)	V	_	-82	-250	mV	$I_C = -1A$, $I_B = -100mA$	
Collector-Enritter Saturation Voltage (Note 10)	$V_{CE(SAT)}$	_	-206	-500	mV	$I_C = -3A$, $I_B = -300mA$	
Base-Emitter Saturation Voltage (Note 10)	$V_{BE(SAT)}$	_	-0.87	-1	V	$I_C = -1A$, $I_B = -100mA$	
Base-Emitter Turn-On Voltage (Note 10)	$V_{BE(ON)}$	_	-0.78	-0.9	V	$I_{C} = -1A$, $V_{CE} = -2V$	
	h _{FE}	70	168	_	_	$I_C = -50 \text{mA}, V_{CE} = -2 \text{V}$	
DC Current Gain (Note 10)		100	155	300	_	$I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$	
DC Current Gain (Note 10)		80	145	_	_	$I_{C} = -1A, V_{CE} = -2V$	
		40	117	_	_	$I_{C} = -2A$, $V_{CE} = -2V$	
Current Gain-Bandwidth Product	f_{T}	100	140	_	MHz	V _{CE} = -5V, I _C = -100mA f = 100MHz	
Turn-On Time	t _{ON}	_	40		ns	V _{CC} = -10V, I _C = -500mA	
Turn-Off Time	t _{OFF}	_	450	_	ns	$I_{B1} = -I_{B2} = -50 \text{mA}$	
Output Capacitance	C _{OBO}	_	_	30	pF	V _{CB} = -10V, f = 1MHz	

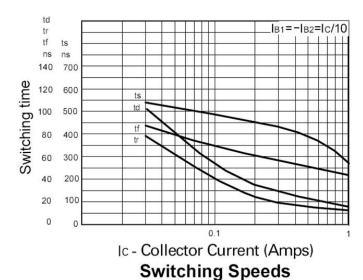
Note: 10. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

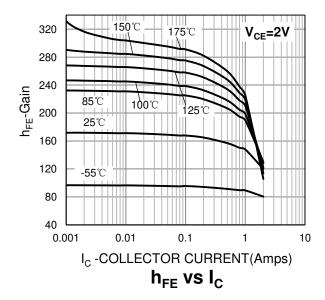


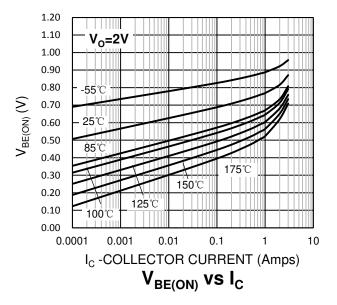
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)









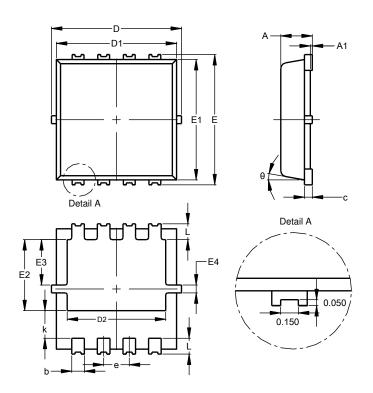




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

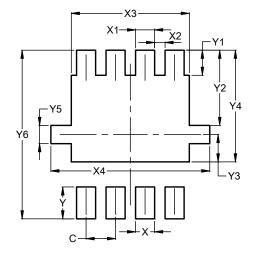


PowerDI3333-8 (SWP)					
(Type UX)					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A 1	0.00	0.05			
Ь	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E3	0.95	1.35	1.15		
E4	0.10	0.30	0.20		
е	_	-	0.65		
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.600
X4	3.500
Υ	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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